

Silicon PNP Power Transistors

2SA1133 2SA1133A

DESCRIPTION

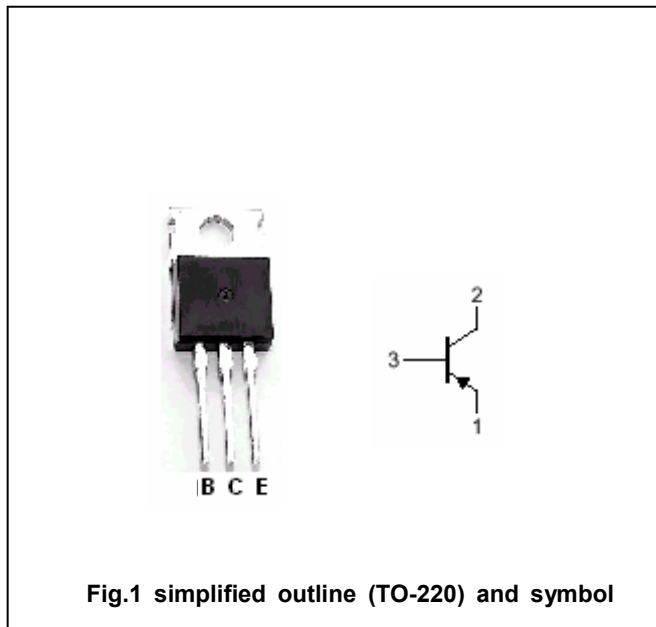
- With TO-220 package
- High breakdown voltage
- High power dissipation
- Complement to type 2SC2660/2660A

APPLICATIONS

- For power amplifier and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-200	V
V _{CEO}	Collector-emitter voltage	2SA1133	-150	V
		2SA1133A	-180	
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-2.0	A
I _{CM}	Collector current-peak		-3.0	A
P _T	Total power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1133	I _C =-5mA, I _B =0	-150		V
		2SA1133A		-180		
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-0.5mA, I _E =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.5mA, I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-400mA; V _{CE} =-10V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-200V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-150mA; V _{CE} =-10V	60		240	
h _{FE-2}	DC current gain	I _C =-400mA; V _{CE} =-10V	50			

◆ h_{FE-1} Classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE

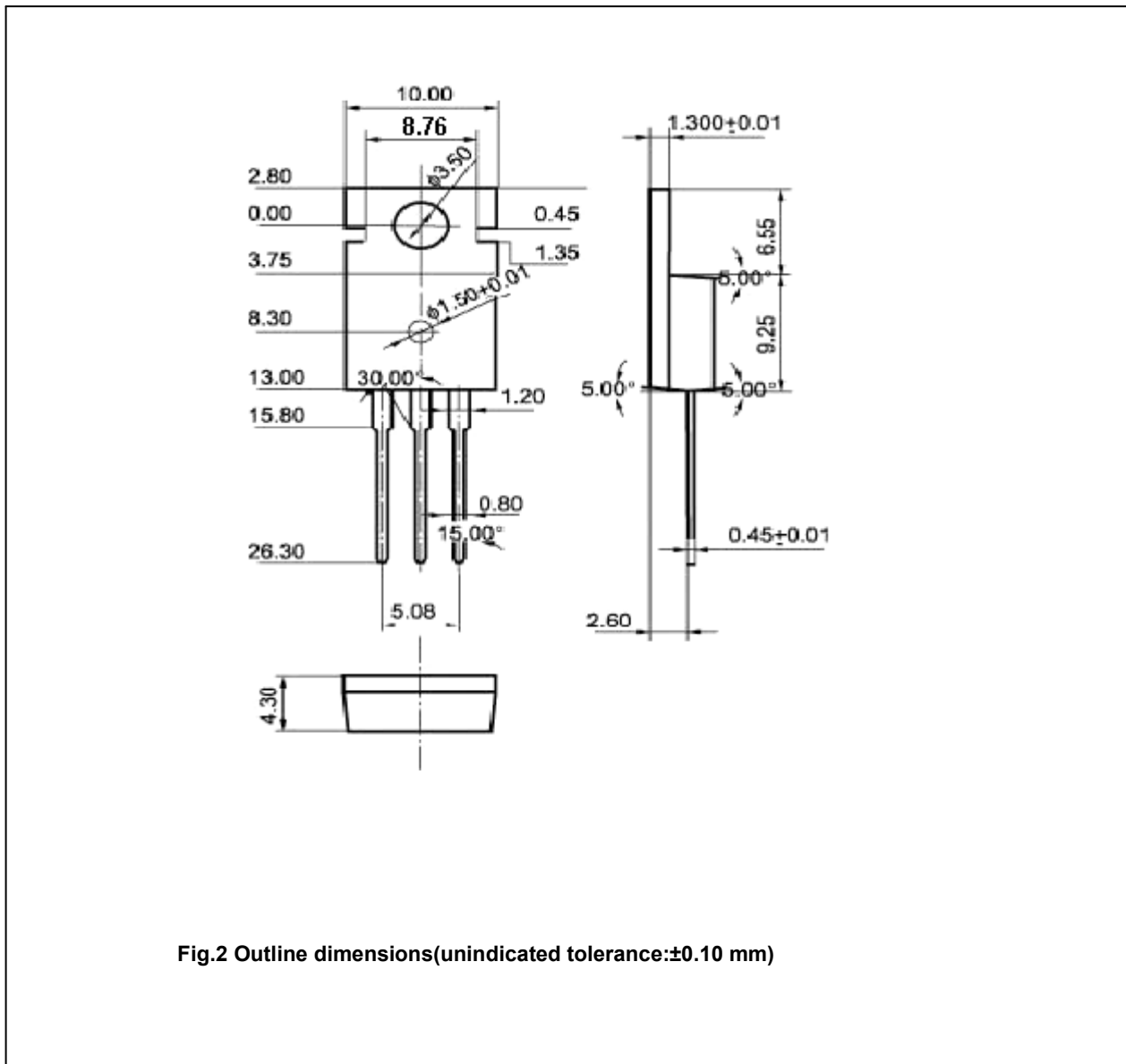


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)